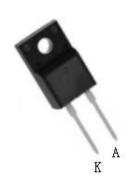
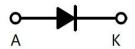


FRED Ultrafast Soft Recovery Diode, 16A

Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low I_R value
- High surge capacity
- Epitaxial chip construction





Product Summary		
VR	600 V	
lf(AV)	16A	
trr	27 ns	

Description/Applications

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes offers the need as snubber in most applications. These devices are ideally suited for HF welding power converters and other applications where the switching losses are not significant portion of the total losses.

Absolute Maximum Ratings				
Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	Vrrm		600	V
Continuous forward current	lf(AV)	Tc =110°C	16	
Single pulse forward current	IFSM	Tc =25°C	128	А
Maximum repetitive forward current	IFRM	Square wave, 20kHZ	30	
Operating junction	Тј		175	°C
Storage temperatures	Tstg		-55 to +175	°C

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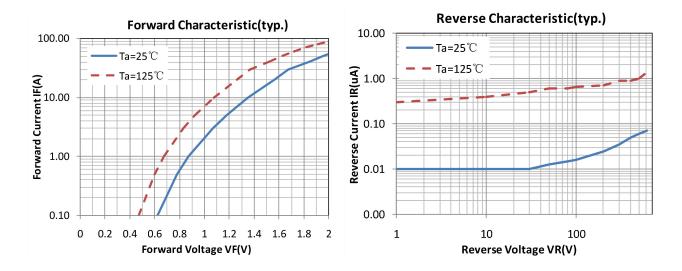


Parameter	Symbol	Test Conditions	Min	Тур.	Max.	Units
Breakdown voltage	VBR,	IR=100μA	600			
Blocking voltage	V_R					
Forward voltage (Per Diode)	VF	IF=16A		1.40	1.60	V
		IF=16A, Tj =125°C		1.22	1.40	
Reverse leakage current(Per Diode)	IR -	VR= VRRM			20	μΑ
		Tj=150°C, Vr=600V			200	
Reverse recovery time(Per Diode)	+	I _F =0.5A, I _R =1A, I _{RR} =0.25A		35	45	ns
	trr	I _F =1A,V _R =30V, di/ <i>dt</i> =200A/us		27	35	

Thermal characteristics

Paramter	Symbol	Тур	Units
Junction-to-Case	$R_{ heta JC}$	2.0	°C/W

Electrical performance (typic)

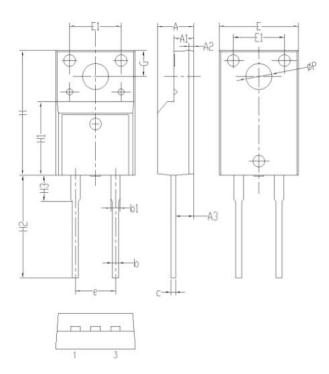


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Package Information

TO-220F-2L PACKAGE



Symbol	Dimensions(millimeters	
Symbol	Min.	Max.
Α	4.35	4.75
A1	2.30	2.70
A2	0.40	0.80
A3	2.10	2.50
b	0.60	1.00
b1	1.00	1.40
С	0.30	0.70
е	4.60	5.40
E	9.80	10.2
E1	6.30	6.70
Н	15.6	16.0
H1	8.80	9.20
H2	12.9	13.5
H3	3.10	3.50
G	3.10	3.50
ФР	3.10	3.50

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